

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A manufacturing method of an SOI wafer, comprising:  
~~bonding a wafer for active layer with a supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then~~  
~~reducing a film thickness in a part of said active layer wafer of said bonded wafer to thereby form an SOI layer for manufacturing said SOI wafer; preparing a supporting wafer contains comprising boron by in an amount of  $9 \times 10^{18}$  atoms/cm<sup>3</sup> or more; and~~  
~~forming a rear surface insulating film on a one surface ~~opposite to the bonding surface~~ of the said supporting wafer prior to said bonding. ;~~  
ion-implanting hydrogen gas or a noble gas element to an active layer wafer to thereby form an ion-implanted layer in said active layer wafer;  
bonding said active layer wafer with a the other surface of said supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then  
heat treating said bonded wafer to thereby induce cleavage in a portion of said bonded wafer at the site of the ion-implanted layer as an interface to thereby form an SOI layer with said remaining active layer wafer for manufacturing said SOI wafer.

2. (Cancelled)

3. (Currently Amended) A manufacturing method of an SOI wafer in accordance with claim 1, ~~in which- wherein~~ a thickness of the SOI layer is less than 0.10  $\mu\text{m}$ .

4, 9 - 21. (Cancelled)